

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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## S200 - 50

200 Watts, 50 Volts, Class AB or C Milcom 1.5 - 30 MHz

### **GENERAL DESCRIPTION**

The S200-50 is a COMMON EMITTER, HF, SSB device intended for operation from a 50 Volts supply. It may be operated in Class A, AB or C. The device exhibits excellent linearity and ruggedness.

#### ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 320 Watts

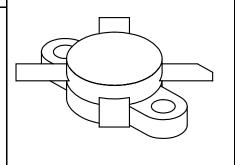
**Maximum Voltage and Current** 

BVces Collector to Emiter Voltage 110 Volts
BVebo Emitter to Base Voltage 4.0 Volts
Ic Collector Current 30 A

**Maximum Temperatures** 

Storage Temperature  $-65 \text{ to } +150^{\circ}\text{C}$ Operating Junction Temperature  $+150^{\circ}\text{C}$ 

# CASE OUTLINE 55HX, Style 2



## **ELECTRICAL CHARACTERISTICS** @ 25 °C

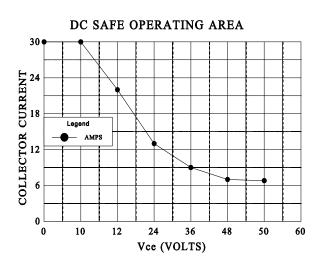
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg ¶c VSWR	Power Output Power Input Power Gain Efficiency Load Mismatch Tolerance	F = 30 MHz Vcc = 50 Volts Class C Bias	200 12	14.5 60	12 30:1	Watts Watts dB %

BVebo	Emitter to Base Breakdown	Ie = 20  mA	4.0			Volts
BVces	Collector to Emitter Breakdown	Ic = 100  mA	110			Volts
BVceo	Collector to Emitter Breakdown	Ie = 200  mA	70			Volts
Cob	Output Capacitance	Vcb = 50V, F = 1 MHz		300		pF
$\mathbf{h}_{\mathbf{FE}}$	DC - Current Gain	Vce = 5 V, Ic = 1 A	10			_
θјс	Thermal Resistance				.55	°C/W

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#### POWER OUTPUT vs POWER INPUT

